NSN 5961-01-119-8257

Transistor - Page 1 of 1



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Inclosure Material:

Metal

Overall Length:

0.450 inches

Overall Diameter:

1.050 inches

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact

Electrode Internally-electrically Connected To Case:

Collector

Mounting Method:

Unthreaded hole

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

-100.0 breakdown voltage, collector-to-base, emitter open and -100.0 breakdown voltage, collector-to-emitter, with base short-circuited to emitter and 180.0 breakdown voltage, collector-to-emitter, base open and -5.5 breakdown voltage, emitter-to-base, collector open

Current Rating Per Characteristic:

-10.00 amperes source cutoff current and -4.00 amperes source cutoff current

Power Rating Per Characteristic:

5.0 watts small-signal input power, common-collector preset

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Special Features:

Junction pattern arrangement: npn

Nuclear Hardness Critical Feature:

Hardened

Terminal Type And Quantity:

1 case and 2 uninsulated wire lead

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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